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List of Publications by Year in descending order

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1,025 papers	54,430 citations	1229 113 h-index	3171 192 g-index
1040 all docs	1040 docs citations	1040 times ranked	19941 citing authors

#	Article	IF	Citations
1	Nano-porous GaN cladding and scattering loss in edge emitting laser diodes. Optics Express, 2022, 30, 2759.	1.7	12
2	Demonstration of ultra-small 5 Ã— 5 <i>Î¼</i>m2 607â€‰nm InGaN amber micro-light-emitting diodes with an external quantum efficiency over 2%. Applied Physics Letters, 2022, 120, .	1.5	13
3	Designs for III-nitride edge-emitting laser diodes with tunnel junction contacts for low internal optical absorption loss. Optical Engineering, 2022, 61, .	0.5	0
4	Computational design and optimization of nanostructured AlN deep-UV grating reflectors. Optics Express, 2022, 30, 12120.	1.7	1
5	Acceptor traps as the source of holes in p-type N-polar GaN/(AlN/AlGaN) superlattices. Applied Physics Letters, 2022, 120, .	1.5	5
6	Inverted N-polar blue and blue-green light emitting diodes with high power grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2022, 120, 101104.	1.5	2
7	Red InGaN micro-light-emitting diodes (>620â€‰nm) with a peak external quantum efficiency of 4.5% using an epitaxial tunnel junction contact. Applied Physics Letters, 2022, 120, .	1.5	33
8	Progress of InGaN-Based Red Micro-Light Emitting Diodes. Crystals, 2022, 12, 541.	1.0	23
9	Size dependent characteristics of AlGaN-based deep ultraviolet micro-light-emitting-diodes. Applied Physics Express, 2022, 15, 064003.	1.1	7
10	Low Forward Voltage III-Nitride Red Micro-Light-Emitting Diodes on a Strain Relaxed Template with an InGaN Decomposition Layer. Crystals, 2022, 12, 721.	1.0	9
11	Improved Vertical Carrier Transport for Green III-Nitride LEDs Using <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mi>In</mml:mi><mml:mo>,</mml:mo><mml:mi>Ga</mml:mi><mml:mo) Tj ETQq1 1 0.784314 rg BT mathvariant="normal">N</mml:mi></mml:mrow></mml:mrow></mml:math> Alloy Quantum Barriers. Physical Review Applied, 2022, 17, .	1.5	9
12	Designing Highly Directional Luminescent Phased-Array Metasurfaces with Reciprocity-Based Simulations. ACS Omega, 2022, 7, 22477-22483.	1.6	3
13	High external quantum efficiency III-nitride micro-light-emitting diodes. Semiconductors and Semimetals, 2021, 106, 95-121.	0.4	3
14	Controlling Spontaneous Emission with Nanohole-Based Phased-Array Metasurfaces. , 2021, , .		0
15	Metalorganic chemical vapor deposition-grown tunnel junctions for low forward voltage InGaN light-emitting diodes: epitaxy optimization and light extraction simulation. Semiconductor Science and Technology, 2021, 36, 035019.	1.0	9
16	Study of surface roughness of lifted-off epitaxial lateral overgrown GaN layers for the n-DBR mirror of a III-nitride vertical-cavity surface emitting laser. Applied Physics Express, 2021, 14, 031002.	1.1	4
17	Blue semipolar InGaN microcavity light-emitting diode with varying cavity lengths from 113 to 290Ânm. Applied Physics Express, 2021, 14, 042003.	1.1	3
18	InN Quantum Dots by Metalorganic Chemical Vapor Deposition for Optoelectronic Applications. Frontiers in Materials, 2021, 8, .	1.2	1

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19	Damage-free substrate removal technique: wet undercut etching of semipolar 202Â¯1 laser structures by incorporation of un/relaxed sacrificial layer single quantum well. Japanese Journal of Applied Physics, 2021, 60, 050901.	0.8	0
20	Role of V-defect density on the performance of III-nitride green LEDs on sapphire substrates. Journal of Crystal Growth, 2021, 560-561, 126048.	0.7	13
21	2DEGs formed in AlN/GaN HEMT structures with AlN grown at low temperature. Applied Physics Letters, 2021, 118, .	1.5	6
22	Demonstration of high efficiency cascaded blue and green micro-light-emitting diodes with independent junction control. Applied Physics Letters, 2021, 118, .	1.5	17
23	Light-emitting metalenses and meta-axicons for focusing and beaming of spontaneous emission. Nature Communications, 2021, 12, 3591.	5.8	31
24	Growth by MOCVD and photoluminescence of semipolar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si5.svg"><mml:mrow><mml:mo stretchy="false">(</mml:mo><mml:mn>20</mml:mn><mml:mover) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 547 Td (accent="true"><mml	0.7	4
25	Growt Fully transparent metal organic chemical vapor deposition-grown cascaded InGaN micro-light-emitting diodes with independent junction control. Optics Express, 2021, 29, 22001.	1.7	9
26	Demonstration of high wall-plug efficiency III-nitride micro-light-emitting diodes with MOCVD-grown tunnel junction contacts using chemical treatments. Applied Physics Express, 2021, 14, 086502.	1.1	13
27	Metalorganic chemical vapor deposition of InN quantum dots and nanostructures. Light: Science and Applications, 2021, 10, 150.	7.7	4
28	Limiting factors of GaN-on-GaN LED. Semiconductor Science and Technology, 2021, 36, 095035.	1.0	2
29	N-face GaN substrate roughening for improved performance GaN-on-GaN LED. Microelectronics International, 2021, 38, 93-98.	0.4	2
30	Size-independent peak external quantum efficiency (>2%) of InGaN red micro-light-emitting diodes with an emission wavelength over 600â€‰nm. Applied Physics Letters, 2021, 119, .	1.5	39
31	Highly Conductive n-Al0.65Ga0.35N Grown by MOCVD Using Low V/III Ratio. Crystals, 2021, 11, 1006.	1.0	12
32	High internal quantum efficiency of long wavelength InGaN quantum wells. Applied Physics Letters, 2021, 119, .	1.5	10
33	Growth of highly relaxed InGaN pseudo-substrates over full 2-in. wafers. Applied Physics Letters, 2021, 119, .	1.5	31
34	Demonstration of relaxed InGaN-based red LEDs grown with high active region temperature. Applied Physics Express, 2021, 14, 101002.	1.1	32
35	Patterned IIIâ€Nitrides on Porous GaN: Extending Elastic Relaxation from the Nanoâ€•to the Micrometer Scale. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100234.	1.2	9
36	Growth of highly conductive Al-rich AlGaN:Si with low group-III vacancy concentration. AIP Advances, 2021, 11, .	0.6	13

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37	Germicidal ultraviolet LEDs: a review of applications and semiconductor technologies. Semiconductor Science and Technology, 2021, 36, 123001.	1.0	32
38	Realization of III-Nitride c-Plane microLEDs Emitting from 470 to 645 nm on Semi-Relaxed Substrates Enabled by V-Defect-Free Base Layers. Crystals, 2021, 11, 1168.	1.0	6
39	Improving backside (N-face) GaN substrate roughening by pre-annealing for GaN-on-GaN LED. Optical Materials, 2021, 121, 111570.	1.7	3
40	Enhanced external quantum efficiency of III-nitride micro-light-emitting diodes using vertical and transparent package. Japanese Journal of Applied Physics, 2021, 60, 020905.	0.8	3
41	High efficiency blue InGaN microcavity light-emitting diode with a 205â€‰nm ultra-short cavity. Applied Physics Letters, 2021, 118, 031102.	1.5	3
42	MOCVD growth of thick V-pit-free InGaN films on semi-relaxed InGaN substrates. Semiconductor Science and Technology, 2021, 36, 015011.	1.0	8
43	Demonstration of ultra-small (<10 Î¼m) 632 nm red InGaN micro-LEDs with useful on-wafer external quantum efficiency (>0.2%) for mini-displays. Applied Physics Express, 2021, 14, 011004.	1.1	96
44	Optical and electrical characterizations of micro-LEDs grown on lower defect density epitaxial layers. Applied Physics Letters, 2021, 119, .	1.5	6
45	InGaN-Based microLED Devices Approaching 1% EQE with Red 609 nm Electroluminescence on Semi-Relaxed Substrates. Crystals, 2021, 11, 1364.	1.0	30
46	Effects of activation method and temperature to III-nitride micro-light-emitting diodes with tunnel junction contacts grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2021, 119, .	1.5	7
47	Reduction of efficiency droop in c-plane InGaN/GaN light-emitting diodes using a thick single quantum well with doped barriers. Applied Physics Letters, 2021, 119, .	1.5	10
48	Properties of AlN/GaN Heterostructures Grown at Low Growth Temperatures with Ammonia and Dimethylhydrazine. Crystals, 2021, 11, 1412.	1.0	2
49	High-temperature electroluminescence properties of InGaN red 40â€‰Ã—â€‰40 Î¼ m2 micro-light-emitting diodes with a peak external quantum efficiency of 3.2%. Applied Physics Letters, 2021, 119, .	1.5	21
50	Semipolar {202Â¯1} GaN Edge-Emitting Laser Diode on Epitaxial Lateral Overgrown Wing
. Crystals, 2021, 11, 1563.	1.0	1
51	MOCVD Growth and Characterization of InN Quantum Dots. Physica Status Solidi (B): Basic Research, 2020, 257, 1900508.	0.7	7
52	Inhomogeneous Current Injection and Filamentary Lasing of Semipolar (2021Â¯) Blue GaNâ€Based Verticalâ€Cavity Surfaceâ€Emitting Lasers with Buried Tunnel Junctions. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900718.	0.8	14
53	Polarized monolithic white semipolar (20â€“21) InGaN light-emitting diodes grown on high quality (20â€“21) GaN/sapphire templates and its application to visible light communication. Nano Energy, 2020, 67, 104236.	8.2	53
54	Reviewâ€”Progress in High Performance III-Nitride Micro-Light-Emitting Diodes. ECS Journal of Solid State Science and Technology, 2020, 9, 015012.	0.9	110

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55	Semipolar (20 21 Â¯) InGaN/GaN micro-photodetector for gigabit-per-second visible light communication. Applied Physics Express, 2020, 13, 014001.	1.1	39
56	Research Toward a Heterogeneously Integrated InGaN Laser on Silicon. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900770.	0.8	11
57	Lift-off of semipolar blue and green III-nitride LEDs grown on free-standing GaN. Applied Physics Letters, 2020, 117, 021104.	1.5	2
58	High polarization and fast modulation speed of dual wavelengths electroluminescence from semipolar (20-21) micro light-emitting diodes with indium tin oxide surface grating. Applied Physics Letters, 2020, 117, .	1.5	16
59	Comparison between standing transparent mirrorless packaging and planar-mounted packaging for GaN-on-GaN LEDs. Journal of Physics: Conference Series, 2020, 1535, 012056.	0.3	0
60	Color-tunable <10â€‰<i> Î¼ </i>m square InGaN micro-LEDs on compliant GaN-on-porous-GaN pseudo-substrates. Applied Physics Letters, 2020, 117, .	1.5	44
61	Transmission Geometry Laser Lighting with a Compact Emitter. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000391.	0.8	4
62	Quasiordered, subwavelength TiO2 hole arrays with tunable, omnidirectional color response. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	4
63	Method of growing elastically relaxed crack-free AlGaN on GaN as substrates for ultra-wide bandgap devices using porous GaN. Applied Physics Letters, 2020, 117, .	1.5	15
64	7.4-Gbit/s Visible-Light Communication Utilizing Wavelength-Selective Semipolar Micro-Photodetector. IEEE Photonics Technology Letters, 2020, , 1-1.	1.3	11
65	Quantitative investigation of indium distribution in InN wetting layers and dots grown by metalorganic chemical vapor deposition. Applied Physics Express, 2020, 13, 065005.	1.1	4
66	Unidirectional luminescence from InGaN/GaN quantum-well metasurfaces. Nature Photonics, 2020, 14, 543-548.	15.6	64
67	Anomalous carrier dynamics and localization effects in nonpolar m-plane InGaN/GaN quantum wells at high temperatures. Nano Energy, 2020, 76, 105013.	8.2	3
68	Flow modulation metalorganic vapor phase epitaxy of GaN at temperatures below 600 ÂºC. Semiconductor Science and Technology, 2020, 35, 095014.	1.0	7
69	Demonstration of Efficient Semipolar 410 nm Violet Laser Diodes Heteroepitaxially Grown on High-Quality Low-Cost GaN/Sapphire Substrates. ACS Applied Electronic Materials, 2020, 2, 1874-1879.	2.0	6
70	Room-Temperature Continuous-Wave Electrically Driven Semipolar (202Ì…1) Blue Laser Diodes Heteroepitaxially Grown on a Sapphire Substrate. ACS Photonics, 2020, 7, 1662-1666.	3.2	11
71	Growth of strain-relaxed InGaN on micrometer-sized patterned compliant GaN pseudo-substrates. Applied Physics Letters, 2020, 116, .	1.5	38
72	An approach to remove homoepitaxially grown GaN layers by cleavage from the substrate surface. Applied Physics Express, 2020, 13, 041003.	1.1	3

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73	High-Speed Nonpolar InGaN/GaN Superluminescent Diode With 2.5 GHz Modulation Bandwidth. IEEE Photonics Technology Letters, 2020, 32, 383-386.	1.3	13
74	Revealing the importance of light extraction efficiency in InGaN/GaN microLEDs via chemical treatment and dielectric passivation. Applied Physics Letters, 2020, 116, .	1.5	94
75	Comparison of size-dependent characteristics of blue and green InGaN microLEDs down to 1â€‰ Î¼ m in diameter. Applied Physics Letters, 2020, 116, .	1.5	141
76	AlGaN Deep-Ultraviolet Light-Emitting Diodes Grown on SiC Substrates. ACS Photonics, 2020, 7, 554-561.	3.2	59
77	Development of efficient semipolar InGaN long wavelength light-emitting diodes and blue laser diodes grown on a high quality semipolar GaN/sapphire template. JPhys Photonics, 2020, 2, 031003.	2.2	7
78	Metalorganic chemical vapor deposition grown n-InGaN/n-GaN tunnel junctions for micro-light-emitting diodes with very low forward voltage. Semiconductor Science and Technology, 2020, 35, 125023.	1.0	23
79	Barriers to carrier transport in multiple quantum well nitride-based <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>c</mml:mi></mml:math> -plane green light emitting diodes. Physical Review Materials, 2020, 4, .	0.9	16
80	Semipolar group III-nitride distributed-feedback blue laser diode with Indium tin oxide surface grating. , 2020, , .		2
81	Highly efficient InGaN-based LED with pre-roughening backside of GaN substrate. Journal of the Optical Society of America B: Optical Physics, 2020, 37, 1614.	0.9	6
82	Improved performance of AlGaInP red micro-light-emitting diodes with sidewall treatments. Optics Express, 2020, 28, 5787.	1.7	105
83	Electrically driven, polarized, phosphor-free white semipolar (20-21) InGaN light-emitting diodes grown on semipolar bulk GaN substrate. Optics Express, 2020, 28, 13569.	1.7	13
84	560â€…nm InGaN micro-LEDs on low-defect-density and scalable (20-21) semipolar GaN on patterned sapphire substrates. Optics Express, 2020, 28, 18150.	1.7	13
85	Tamm plasmons in metal/nanoporous GaN distributed Bragg reflector cavities for active and passive optoelectronics. Optics Express, 2020, 28, 17934.	1.7	32
86	Size-independent low voltage of InGaN micro-light-emitting diodes with epitaxial tunnel junctions using selective area growth by metalorganic chemical vapor deposition. Optics Express, 2020, 28, 18707.	1.7	26
87	Dependence of carrier escape lifetimes on quantum barrier thickness in InGaN/GaN multiple quantum well photodetectors. Optics Express, 2020, 28, 23796.	1.7	15
88	Violet semipolar (20-2-1) InGaN microcavity light-emitting diode with a 200â€…nm ultra-short cavity length. Optics Express, 2020, 28, 29991.	1.7	8
89	Fabrication and chemical lift-off of sub-micron scale III-nitride LED structures. Optics Express, 2020, 28, 35038.	1.7	11
90	Color-changing refractive index sensor based on Fano-resonant filtering of optical modes in a porous dielectric Fabry-PÃ©rot microcavity. Optics Express, 2020, 28, 28226.	1.7	6

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91	High performance of a semipolar InGaN laser with a phase-shifted embedded hydrogen silsesquioxane (HSQ) grating. Optics Letters, 2020, 45, 5844.	1.7	5
92	Superlattice hole injection layers for UV LEDs grown on SiC. Optical Materials Express, 2020, 10, 2171.	1.6	11
93	Compliant Micron-Sized Patterned InGaN Pseudo-Substrates Utilizing Porous GaN. Materials, 2020, 13, 213.	1.3	22
94	Toward heteroepitaxially grown semipolar GaN laser diodes under electrically injected continuous-wave mode: From materials to lasers. Applied Physics Reviews, 2020, 7, .	5.5	7
95	1.5-Gbit/s Filter-free Optical Communication Link based on Wavelength-selective Semipolar (20 21 Â¯) InGaN/GaN Micro-photodetector. , 2020, , .		0
96	Blue semipolar III-nitride vertical-cavity surface-emitting lasers. , 2020, , .		1
97	Size-independent peak efficiency of III-nitride micro-light-emitting-diodes using chemical treatment and sidewall passivation. Applied Physics Express, 2019, 12, 097004.	1.1	132
98	High-Temperature Polarization-Free III-Nitride Solar Cells with Self-Cooling Effects. ACS Photonics, 2019, 6, 2096-2103.	3.2	28
99	Reduced dislocation density and residual tension in AlN grown on SiC by metalorganic chemical vapor deposition. Applied Physics Letters, 2019, 115, .	1.5	29
100	Fabrication of relaxed InGaN pseudo-substrates composed of micron-sized pattern arrays with high fill factors using porous GaN. Semiconductor Science and Technology, 2019, 34, 115020.	1.0	30
101	Characterization of InGaN quantum dots grown by metalorganic chemical vapor deposition. Semiconductor Science and Technology, 2019, 34, 125002.	1.0	6
102	Impact of a Strained Periodic Multilayer on the Surface and Crystal Quality of a Semipolar (11â€“22) GaN Template. Crystal Growth and Design, 2019, 19, 6092-6099.	1.4	9
103	Infrared luminescence from N-polar InN quantum dots and thin films grown by metal organic chemical vapor deposition. Applied Physics Letters, 2019, 114, 241103.	1.5	14
104	Properties of N-polar InGaN/GaN quantum wells grown with triethyl gallium and triethyl indium as precursors. Semiconductor Science and Technology, 2019, 34, 075017.	1.0	9
105	Interwell carrier transport in InGaN/(In)GaN multiple quantum wells. Applied Physics Letters, 2019, 114, .	1.5	21
106	Reduction of Saturation Voltage in InGaAs-Channel/InGaN-Drain Vertical FETs and the role of traps at the InGaAs/InGaN junction. , 2019, , .		0
107	Demonstration of Electrically Injected Semipolar Laser Diodes Grown on Low-Cost and Scalable Sapphire Substrates. ACS Applied Materials & Interfaces, 2019, 11, 47106-47111.	4.0	13
108	Investigation of oxygen and other impurities and their effect on the transparency of a Na flux grown GaN crystal. Journal of Crystal Growth, 2019, 508, 50-57.	0.7	12

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109	Fabrication technology for high light-extraction ultraviolet thin-film flip-chip (UV TFFC) LEDs grown on SiC. Semiconductor Science and Technology, 2019, 34, 035007.	1.0	33
110	Semipolar InGaN blue laser diodes with a low optical loss and a high material gain obtained by suppression of carrier accumulation in the p-waveguide region. Japanese Journal of Applied Physics, 2019, 58, 020902.	0.8	13
111	Compensation effects of high oxygen levels in semipolar AlGaN electron blocking layers and their mitigation via growth optimization. Journal of Crystal Growth, 2019, 507, 118-123.	0.7	8
112	Semipolar III-nitride laser diodes for solid-state lighting. , 2019, , .		2
113	Efficient tunnel junction contacts for high-power semipolar III-nitride edge-emitting laser diodes. Optics Express, 2019, 27, 8327.	1.7	14
114	Electrical injection of a 440nm InGaN laser with lateral confinement by nanoporous-GaN. Optics Express, 2019, 27, 22764.	1.7	12
115	Demonstration of blue semipolar (202Â¯1Â¯) GaN-based vertical-cavity surface-emitting lasers. Optics Express, 2019, 27, 23707.	1.7	20
116	Study of efficient semipolar (11-22) InGaN green micro-light-emitting diodes on high-quality (11-22) GaN/sapphire template. Optics Express, 2019, 27, 24154.	1.7	43
117	Realization of thin-film m-plane InGaN laser diode fabricated by epitaxial lateral overgrowth and mechanical separation from a reusable growth substrate. Optics Express, 2019, 27, 24717.	1.7	7
118	Strain relaxation of InGaN/GaN multi-quantum well light emitters via nanopatterning. Optics Express, 2019, 27, 30081.	1.7	18
119	Demonstration of GaN-based vertical-cavity surface-emitting lasers with buried tunnel junction contacts. Optics Express, 2019, 27, 31621.	1.7	33
120	Impact of roughening density on the light extraction efficiency of thin-film flip-chip ultraviolet LEDs grown on SiC. Optics Express, 2019, 27, A1074.	1.7	17
121	Continuous-wave operation of a semipolar InGaN distributed-feedback blue laser diode with a first-order indium tin oxide surface grating. Optics Letters, 2019, 44, 3106.	1.7	24
122	Suppression of Anomalously Large Threshold Voltage in Wafer-Bonded Vertical Transistors by Enhancing Critical Field to Impact Ionization. IEEE Transactions on Electron Devices, 2018, 65, 1079-1086.	1.6	3
123	Reduced-droop green IIIâ€“nitride light-emitting diodes utilizing GaN tunnel junction. Applied Physics Express, 2018, 11, 042101.	1.1	29
124	On the optical polarization properties of semipolar (202Â¯1) and (202Â¯1Â¯) InGaN/GaN quantum wells. Journal of Applied Physics, 2018, 123, .	1.1	7
125	Stable, Heat-Conducting Phosphor Composites for High-Power Laser Lighting. ACS Applied Materials & Interfaces, 2018, 10, 5673-5681.	4.0	121
126	Metal-organic chemical vapor deposition of N-polar InN quantum dots and thin films on vicinal GaN. Journal of Applied Physics, 2018, 123, .	1.1	17

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127	Impact of crystal orientation on the modulation bandwidth of InGaN/GaN light-emitting diodes. Applied Physics Letters, 2018, 112, .	1.5	55
128	Spin injection in epitaxial MnGa(111)/GaN(0001) heterostructures. Journal of Applied Physics, 2018, 123, .	1.1	7
129	Semipolar $(20ar{2}1)$ GaN templates on sapphire: 432 nm InGaN light-emitting diodes and light extraction simulations. Applied Physics Express, 2018, 11, 036501.	1.1	14
130	Micro-light-emitting diodes with IIIâ€“nitride tunnel junction contacts grown by metalorganic chemical vapor deposition. Applied Physics Express, 2018, 11, 012102.	1.1	59
131	Carrier dynamics of two distinct localized centers in 530Ânm InGaN green light-emitting diodes. Superlattices and Microstructures, 2018, 113, 684-689.	1.4	6
132	Comparing electrical characteristics of in situ and ex situ Al₂O₃/GaN interfaces formed by metalorganic chemical vapor deposition. Applied Physics Express, 2018, 11, 041002.	1.1	4
133	Continuous-wave operation of m-plane GaN-based vertical-cavity surface-emitting lasers with a tunnel junction intracavity contact. Applied Physics Letters, 2018, 112, .	1.5	44
134	Low threading dislocation density aluminum nitride on silicon carbide through the use of reduced temperature interlayers. Journal of Crystal Growth, 2018, 483, 134-139.	0.7	20
135	Direct Measurement of Nanoscale Lateral Carrier Diffusion: Toward Scanning Diffusion Microscopy. ACS Photonics, 2018, 5, 528-534.	3.2	16
136	High reflectivity Ohmic contacts to n-GaN utilizing vacuum annealed aluminum. Semiconductor Science and Technology, 2018, 33, 015015.	1.0	3
137	Multimode Scanning Near-Field Photoluminescence Spectroscopy of InGaN Quantum Wells. , 2018, , .		0
138	Nonpolar GaN-Based Superluminescent Diode with 2.5 GHz Modulation Bandwidth. , 2018, , .		2
139	Optical Gain and Loss Measurements of Semipolar III-nitride Laser Diodes with ITO/thin-p-GaN Cladding Layers. , 2018, , .		1
140	Trade-off between bandwidth and efficiency in semipolar (202Â¯1Â¯) InGaN/GaN single- and multiple-quantum-well light-emitting diodes. Applied Physics Letters, 2018, 112, .	1.5	27
141	Demonstration of enhanced continuous-wave operation of blue laser diodes on a semipolar 202Â¯1Â¯ GaN substrate using indium-tin-oxide/thin-p-GaN cladding layers. Optics Express, 2018, 26, 1564.	1.7	27
142	Development of high performance green c-plane III-nitride light-emitting diodes. Optics Express, 2018, 26, 5591.	1.7	47
143	Semipolar InGaN quantum-well laser diode with integrated amplifier for visible light communications. Optics Express, 2018, 26, A219.	1.7	23
144	Zinc oxide clad limited area epitaxy semipolar III-nitride laser diodes. Optics Express, 2018, 26, 12490.	1.7	4

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145	Investigation of Mg Î´-doping for low resistance N-polar p-GaN films grown at reduced temperatures by MOCVD. Semiconductor Science and Technology, 2018, 33, 095014.	1.0	11
146	An exploratory study of acidic ammonothermal growth in a TZM autoclave at high temperatures. Journal of Crystal Growth, 2018, 499, 85-89.	0.7	5
147	High efficiency of III-nitride micro-light-emitting diodes by sidewall passivation using atomic layer deposition. Optics Express, 2018, 26, 21324.	1.7	213
148	GaN-based vertical-cavity surface-emitting lasers with tunnel junction contacts grown by metal-organic chemical vapor deposition. Applied Physics Express, 2018, 11, 062703.	1.1	51
149	Continuous-wave operation of nonpolar GaN-based vertical-cavity surface-emitting lasers. , 2018, , .		4
150	Semipolar GaN-based laser diodes for Gbit/s white lighting communication: devices to systems. , 2018, , .		9
151	Developments in AlGaN and UV-C LEDs grown on SiC. , 2018, , .		8
152	A violet III-nitride vertical-cavity surface-emitting laser with a MOCVD-grown tunnel junction contact. , 2018, , .		0
153	Direct Pulse Position Modulation of a 410 nm Semipolar GaN Laser Diode for Space Optical Communications. , 2018, , .		0
154	Exploring metalorganic chemical vapor deposition of Si-alloyed Al 2 O 3 dielectrics using disilane. Journal of Crystal Growth, 2017, 464, 54-58.	0.7	6
155	Structural and Optical Properties of Group III Doped Hydrothermal ZnO Thin Films. Journal of Electronic Materials, 2017, 46, 1821-1825.	1.0	8
156	Semipolar InGaN-based superluminescent diodes for solid-state lighting and visible light communications. Proceedings of SPIE, 2017, , .	0.8	6
157	Semipolar IIIâ€“nitride quantum well waveguide photodetector integrated with laser diode for on-chip photonic system. Applied Physics Express, 2017, 10, 042201.	1.1	30
158	Optoelectronic properties of doped hydrothermal ZnO thin films. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600941.	0.8	3
159	Sustained high external quantum efficiency in ultrasmall blue IIIâ€“nitride micro-LEDs. Applied Physics Express, 2017, 10, 032101.	1.1	169
160	Nonpolar and semipolar InGaN/GaN multiple-quantum-well solar cells with improved carrier collection efficiency. Applied Physics Letters, 2017, 110, .	1.5	36
161	Indium segregation in N-polar InGaN quantum wells evidenced by energy dispersive X-ray spectroscopy and atom probe tomography. Applied Physics Letters, 2017, 110, .	1.5	34
162	Metal-organic chemical vapor deposition of high quality, high indium composition N-polar InGaN layers for tunnel devices. Journal of Applied Physics, 2017, 121, 185707.	1.1	18

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163	Smooth and selective photo-electrochemical etching of heavily doped GaN:Si using a mode-locked 355 nm microchip laser. Applied Physics Express, 2017, 10, 011001.	1.1	13
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